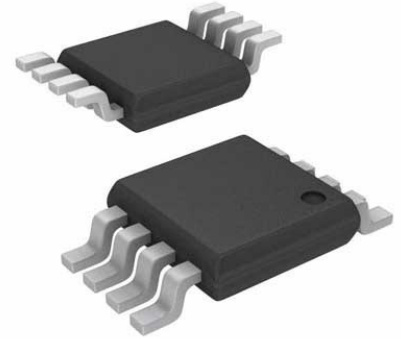


RF Switch SPDT 100MHz to 4GHz 42dB 8-Pin MSOP EP T/R



Images are for reference only

[Inquiry](#)

Manufacturer: [Analog Devices, Inc](#)

Package/Case: MSOP8

Product Type: Switches

RoHS: RoHS Compliant/Lead free 

Lifecycle: Active

General Description

The HMC349AMS8G is a gallium arsenide (GaAs), pseudo-morphic high electron mobility transistor (PHEMT), single-pole, double throw (SPDT) switch specified from 100 MHz to 4 GHz.

The HMC349AMS8G is well suited for cellular infrastructure applications by yielding high isolation of 57 dB, low insertionloss of 0.9 dB, high input IP3 of 52 dBm, and high input P1dB of 34 dBm.

The HMC349AMS8G operates with a single positive supply voltage from 3 V to 5 V and provides a CMOS-/TTL-compatible control interface.

The HMC349AMS8G comes in an 8-lead mini small outline package with an exposed pad.

Key Features

Nonreflective, 50 Ω design

High isolation: 57 dB to 2 GHz

Low insertion loss: 0.9 dB to 2 GHz

High input linearity

1 dB power compression (P1dB): 34 dBm typical

Third-order intercept (IP3): 52 dBm typical

High power handling

33.5 dBm through path

26.5 dBm terminated path

Single positive supply: 3 V to 5 V

CMOS-/TTL-compatible control

All off state control

8-lead mini small outline package with exposed pad (MINI_SO_EP)

Application

Cellular/4G infrastructure

Wireless infrastructure

Mobile radios

Test equipment

Recommended For You

HMC624ALP4E

Analog Devices, Inc

QFN24

HMC952ALP5GE

Analog Devices, Inc

QFN

HMC361S8GE

Analog Devices, Inc

SOP-8

HMC253AQS24E

Analog Devices, Inc

QFN

HMC346MS8G

Analog Devices, Inc

MSOP8

HMC1119LP4ME

Analog Devices, Inc

QFN

HMC659LC5

Analog Devices, Inc

QFN

HMC909LP4E

Analog Devices, Inc

QFN

HMC564LC4

Analog Devices, Inc

QFN

HMC1021LP4E

Analog Devices, Inc

QFN

HMC241AQS16E

Analog Devices, Inc

SSOP16

HMC424LP3E

Analog Devices, Inc

QFN

HMC662LP3E

Analog Devices, Inc

QFN

HMC8038LP4CE

Analog Devices, Inc

QFN16

HMC363S8G

Analog Devices, Inc

SOP8